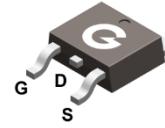
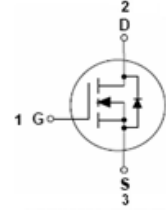


Features

- Low $R_{DS(ON)}$
- Fast switching
- Low gate charge
- Low Reverse transfer capacitances
- HBM: JESD22-A114-B: 1B

HF

TO-252

Mechanical Data

- Case: TO-252
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL8N50D	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	8N50D

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	500	V
Gate-to-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)	I_D	8	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$)		5	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_C = 25^\circ\text{C}$)	I_{DM}	32	A
Single Pulse Avalanche Energy ^{*3}	E_{AS}	400	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	100	W
Operating Junction Temperature Range	T_J	$-55 \sim +150$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.9	1.25	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air ^{*1}	$R_{\theta JA}$	-	-	40	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*2}	$V_{GS} = 10V, I_D = 4A$	-	0.67	0.9	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	3.3	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	1027	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 25V$	-	111	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 1MHz$	-	6	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time ^{*4}	$V_{DD} = 250V$ $I_D = 8A$ $R_G = 10\Omega$	-	18	-	ns
t_r	Turn-on Rise Time ^{*4}		-	20	-	
$t_{d(OFF)}$	Turn-Off Delay Time ^{*4}		-	44	-	
t_f	Turn-Off Fall Time ^{*4}		-	15	-	
Q_G	Total Gate-Charge	$V_{DD} = 400V$	-	23	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	5	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 8A$	-	10	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*2}	$I_{SD} = 8A, V_{GS} = 0V$	-	0.8	1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 8A, V_R = 400V$	-	290	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	2.4	-	μC

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100V, V_{GS} = 15V, L = 10mH$
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

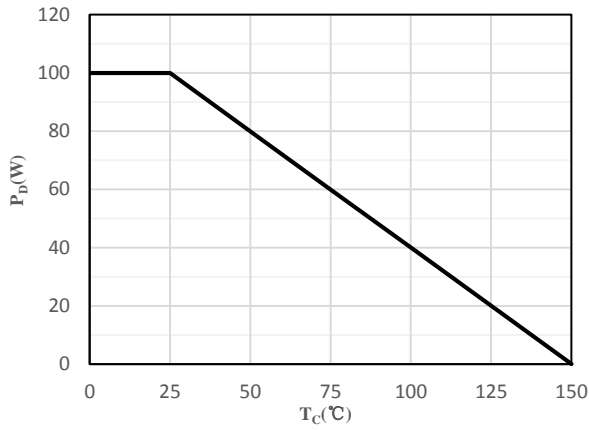


Fig 1 Power Dissipation

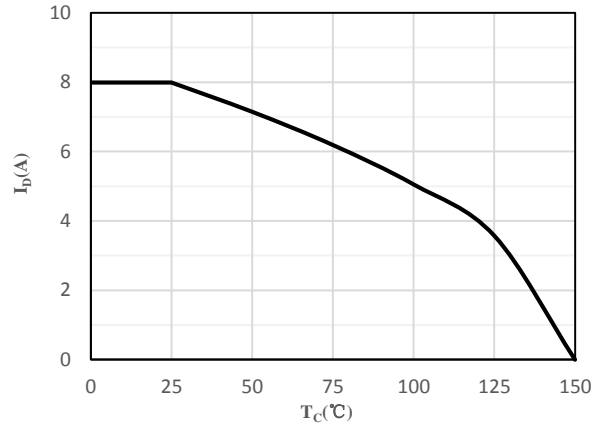


Fig 2 Drain Current

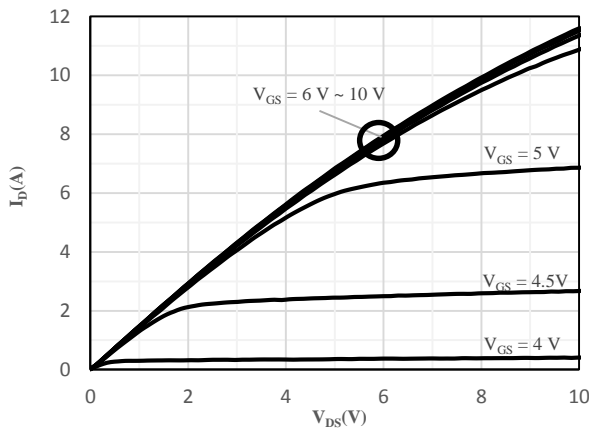


Fig 3 Typical Output Characteristics

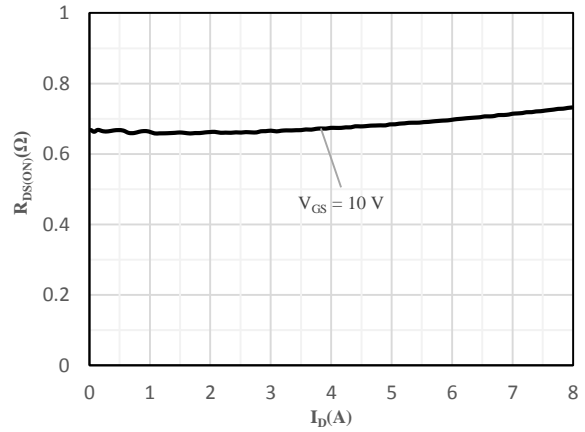


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

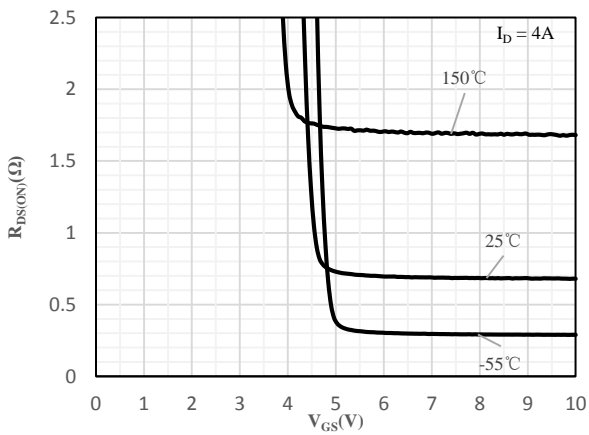


Fig 5 On-Resistance vs. Gate-Source Voltage

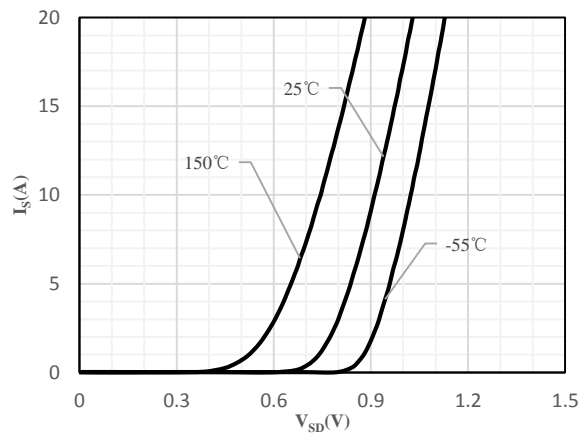


Fig 6 Body-Diode Characteristics

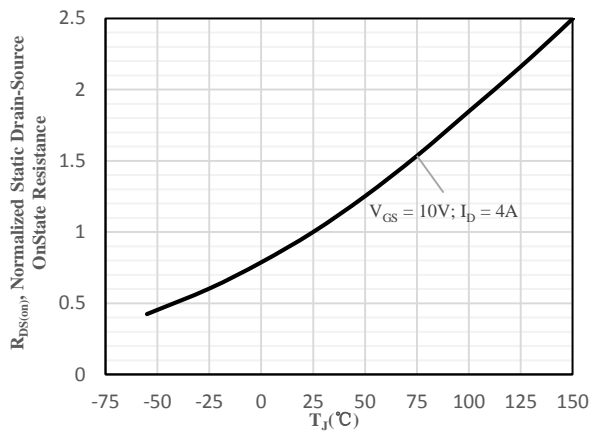


Fig 7 Normalized On-Resistance vs. Junction Temperature

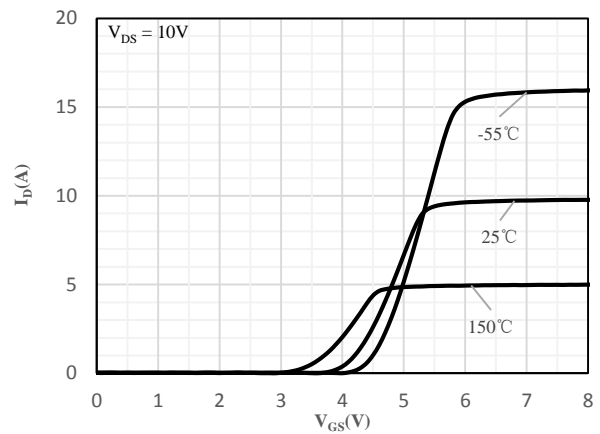


Fig 8 Transfer Characteristics

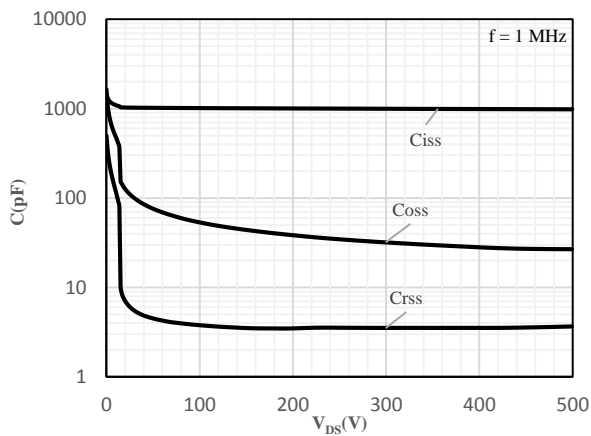


Fig 9 Capacitance Characteristics

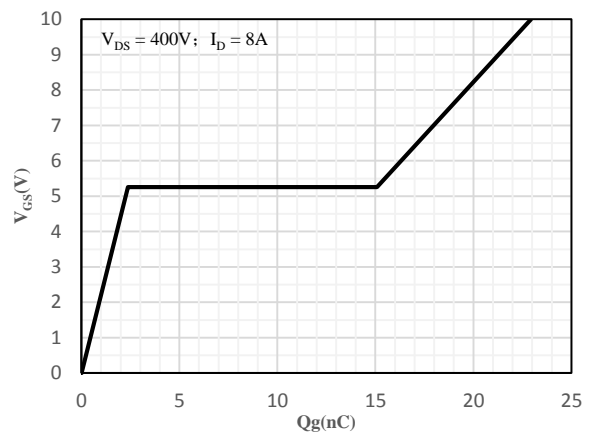


Fig 10 Gate-Charge Characteristics

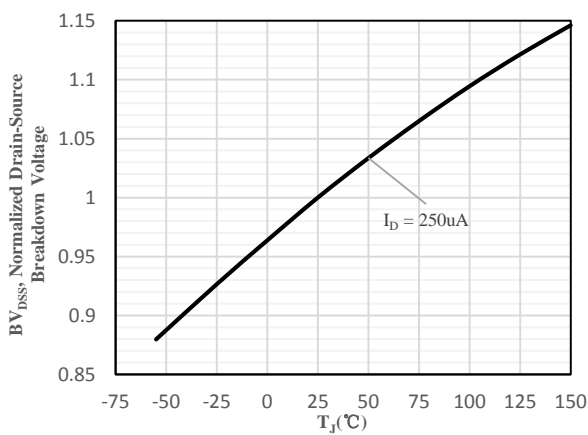


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

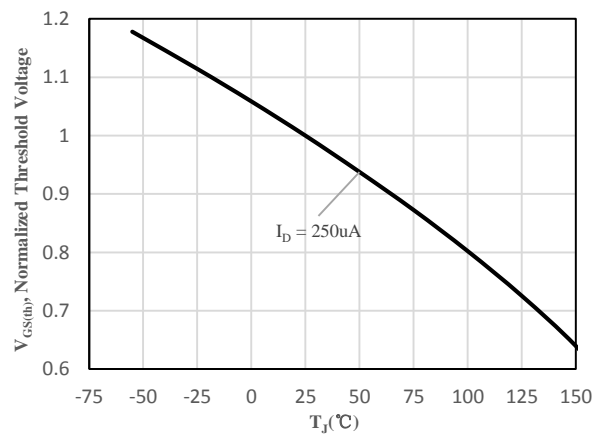


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

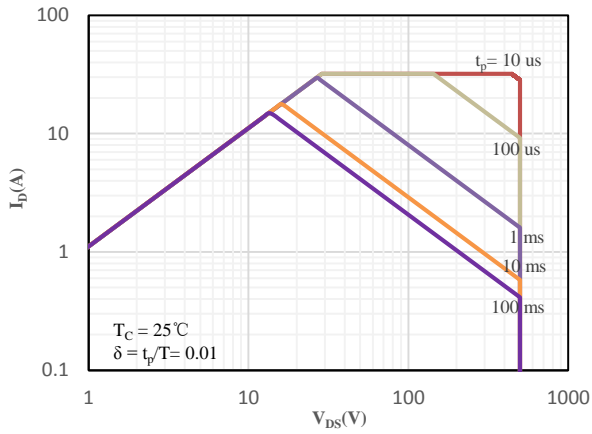


Fig 13 Safe Operation Area (TO-220AB / TO-263)

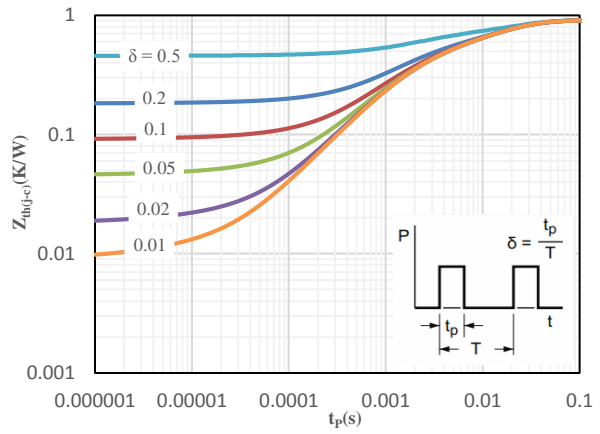
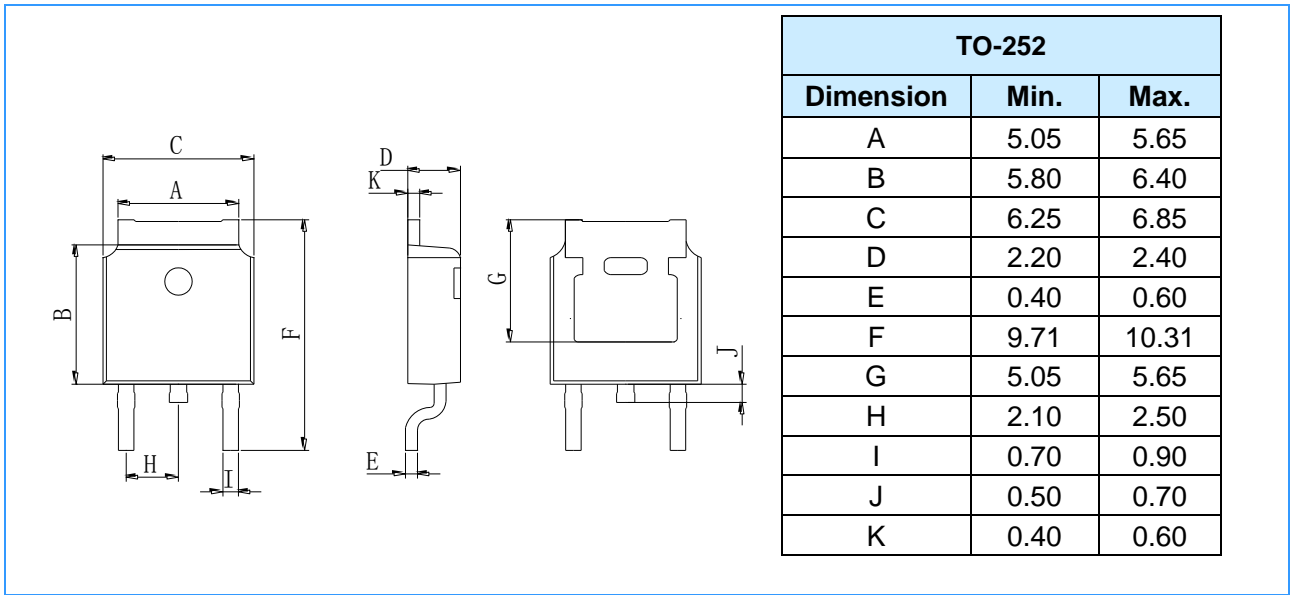
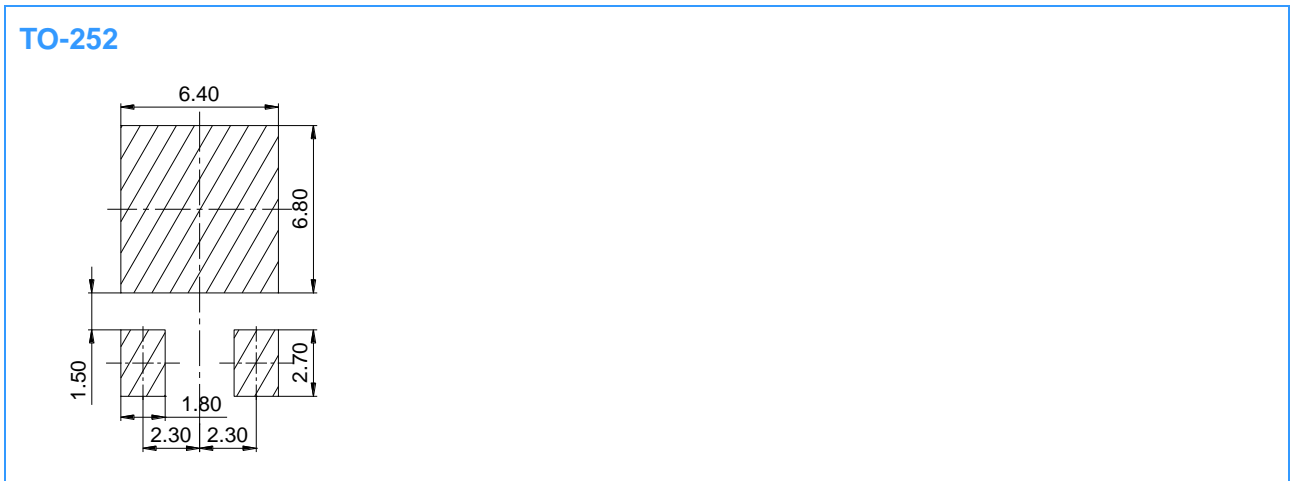


Fig 14 Maximum transient thermal impedance
(TO-220AB / TO-263)

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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